

12 A Three-quadrant triacs high commutation

Rev. 02 — 17 December 2007

Product data sheet

Product profile

1.1 General description

Passivated, new generation, high commutation triacs in a SOT186A full pack plastic package

1.2 Features

- Very high commutation performance maximized at each gate sensitivity
- High isolation voltage
- High immunity to dV/dt

1.3 Applications

- High power motor control e.g. washing
 Refrigeration and air conditioning machines, vacuum cleaners
- Non-linear rectifier-fed motor loads.
- compressors
- Electronic thermostats

1.4 Quick reference data

- $V_{DRM} \le 600 \text{ V (BTA312X-600B/C)}$
- $V_{DRM} \le 800 \text{ V (BTA312X-800B/C)}$
- $I_{TSM} \le 95 \text{ A (t = 20 ms)}$
- I_{GT} \leq 50 mA (BTA312X-series B)
- I_{GT} ≤ 35 mA (BTA312X-series C)
- $I_{T(RMS)} \le 12 A$

Pinning information

Table 1. **Pinning**

Pin	Description	Simplified outline	Symbol
1	main terminal 1 (T1)		
2	main terminal 2 (T2)	mb	T2—T1
3	gate (G)		`G sym051
mb	mounting base; isolated		
		SOT186A (TO-220F)



3. Ordering information

Table 2. Ordering information

Type number	Package					
	Name	Description	Version			
BTA312X-600B	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole;				
BTA312X-600C		3-lead TO-220 'full pack'				
BTA312X-800B						
BTA312X-800C						

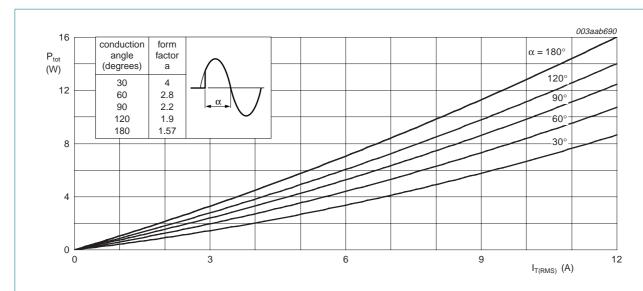
4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

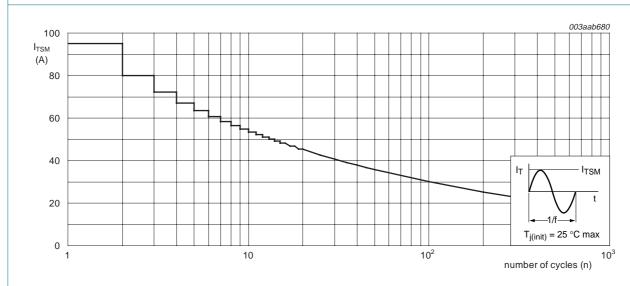
Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage	BTA312X-600B; BTA312X-600C	<u>[1]</u> _	600	V
		BTA312X-800B; BTA312X-800C	-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_h \le 61$ °C; see Figure 4 and 5	-	12	Α
I _{TSM} non-repeti	non-repetitive peak on-state current	full sine wave; $T_j = 25$ °C prior to surge; see Figure 2 and 3			
		t = 20 ms	-	95	Α
		t = 16.7 ms	-	105	Α
I ² t	I ² t for fusing	t = 10 ms	-	45	A ² s
dl _T /dt	rate of rise of on-state current	$I_{TM} = 20 \text{ A}; I_G = 0.2 \text{ A};$ $dI_G/dt = 0.2 \text{ A}/\mu\text{s}$	-	100	A/μs
I _{GM}	peak gate current		-	2	Α
P_{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	+150	°C
T _i	junction temperature		-	125	°C

^[1] Although not recommended, off-state voltages up to 800 V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/µs.



 α = conduction angle

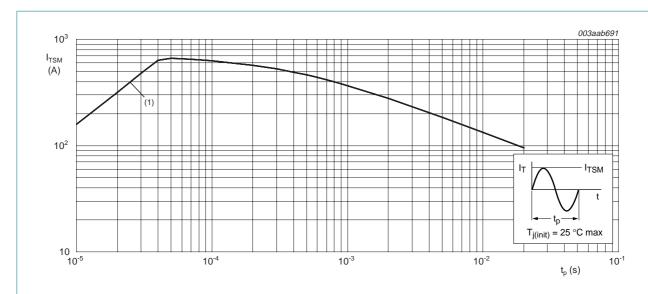
Fig 1. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig 2. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

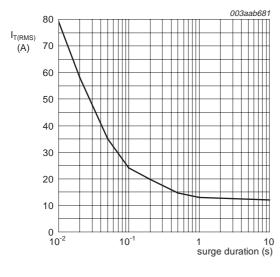
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 $t_p \le 20 \text{ ms}$

(1) dl_T/dt limit

Fig 3. Non-repetitive peak on-state current as a function of pulse duration; maximum values



f = 50 Hz T_h = 61 °C

Fig 4. RMS on-state current as a function of surge duration; maximum values

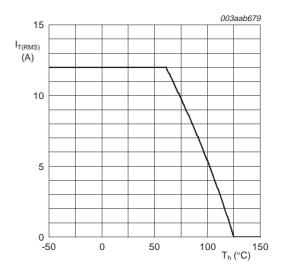
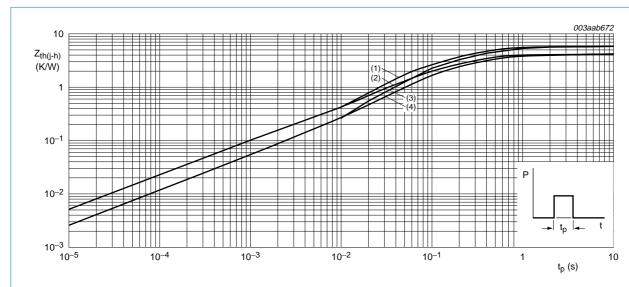


Fig 5. RMS on-state current as a function of heatsink temperature; maximum values

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	full or half cycle; without heatsink compound; see Figure 6	-	-	5.5	K/W
		full or half cycle; with heatsink compound; see Figure 6	-	-	4.0	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W



- (1) Unidirectional (half cycle) without heatsink compound
- (2) Unidirectional (half cycle) with heatsink compound
- (3) Bidirectional (full cycle) without heatsink compound
- (4) Bidirectional (full cycle) with heatsink compound

Fig 6. Transient thermal impedance from junction to heatsink as a function of pulse duration

6. Isolation characteristics

Table 5. Isolation limiting values and characteristics

 $T_h = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	from all three terminals to external heatsink; f = 50 Hz to 60 Hz; sinusoidal waveform; RH ≤ 65 %; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	from pin 2 to external heatsink; f = 1 MHz	-	10	-	pF

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7. Static characteristics

Table 6. Static characteristics

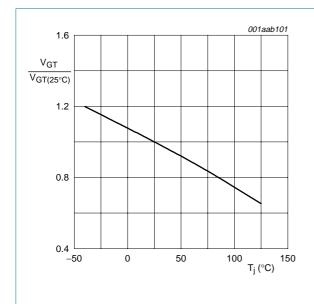
 $T_i = 25 \,^{\circ}C$ unless otherwise specified.

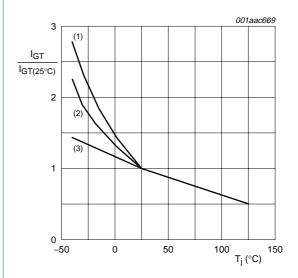
Symbol	Parameter	Conditions		BTA312X-600B BTA312X-800B		BTA312X-600C BTA312X-800C			Unit
			Min	Тур	Max	Min	Тур	Max	
I_{GT}	gate trigger	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ see } \frac{\text{Figure 8}}{}$	'			'	'		
	current	T2+ G+	2	-	50	2	-	35	mΑ
		T2+ G-	2	-	50	2	-	35	mΑ
		T2- G-	2	-	50	2	-	35	mΑ
IL	I _L latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}; \text{ see } \frac{\text{Figure } 10}{}$					-		
		T2+ G+	-	-	60	-	-	50	mΑ
		T2+ G-	-	-	90	-	-	60	mΑ
		T2- G-	-	-	60	-	-	50	mΑ
I _H	holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}; \text{ see } \frac{\text{Figure } 11}{\text{Model}}$	-	-	60	-	-	35	mΑ
V _T	on-state voltage	I _T = 15 A; see <u>Figure 9</u>	-	1.3	1.6	-	1.3	1.6	V
V_{GT}	gate trigger	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ see } \frac{\text{Figure 7}}{}$	-	0.8	1.5	-	0.8	1.5	V
voltage	voltage	$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 ^{\circ}\text{C}$	0.25	0.4	-	0.25	0.4	-	V
I _D	off-state current	$V_D = V_{DRM(max)}$; $T_j = 125 ^{\circ}C$	-	0.1	0.5	-	0.1	0.5	mΑ

8. Dynamic characteristics

Table 7. Dynamic characteristics

Symbol	Parameter	Conditions	BTA312X-600B BTA312X-800B			BTA312X-600C BTA312X-800C			Unit
				Тур	Max	Min	Тур	Max	
dV _D /dt	rate of rise of off-state voltage	$V_{DM} = 0.67 \times V_{DRM(max)}$; $T_j = 125$ °C; exponential waveform; gate open circuit	1000	2000	-	500	-	-	V/μs
dI _{com} /dt	rate of change of commutating current	$V_{DM} = 400 \text{ V}; T_j = 125 ^{\circ}\text{C}; I_{T(RMS)} = 12 \text{ A};$ without snubber; gate open circuit	30	-	-	20	-	-	A/ms
t _{gt}	gate-controlled turn-on time	$I_{TM} = 20 \text{ A; } V_D = V_{DRM(max)}; \ I_G = 0.1 \text{ A;} \\ dI_G/dt = 5 \text{ A}/\mu s$	-	2	-	-	2	-	μs



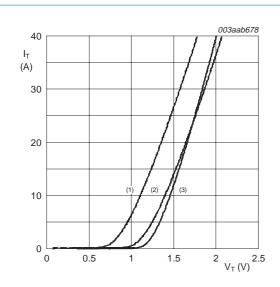


- (1) T2-G-
- (2) T2+ G-
- (3) T2+ G+

Fig 7. Normalized gate trigger voltage as a function of junction temperature

Fig 8. Normalized gate trigger current as a function of junction temperature

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V_o = 1.127 V

- $R_s = 0.027 \Omega$ (1) $T_i = 125 \,^{\circ}\text{C}$; typical values
- (2) $T_i = 125 \,^{\circ}C$; maximum values
- (3) $T_i = 25$ °C; maximum values
- Fig 9. On-state current as a function of on-state voltage

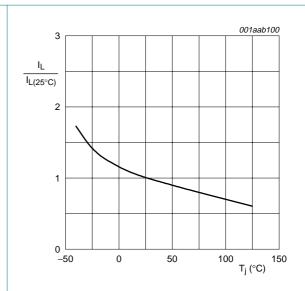


Fig 10. Normalized latching current as a function of junction temperature

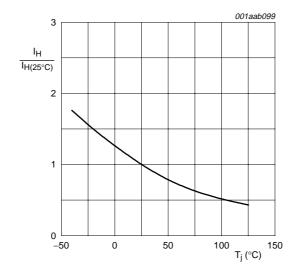


Fig 11. Normalized holding current as a function of junction temperature

9. Package information

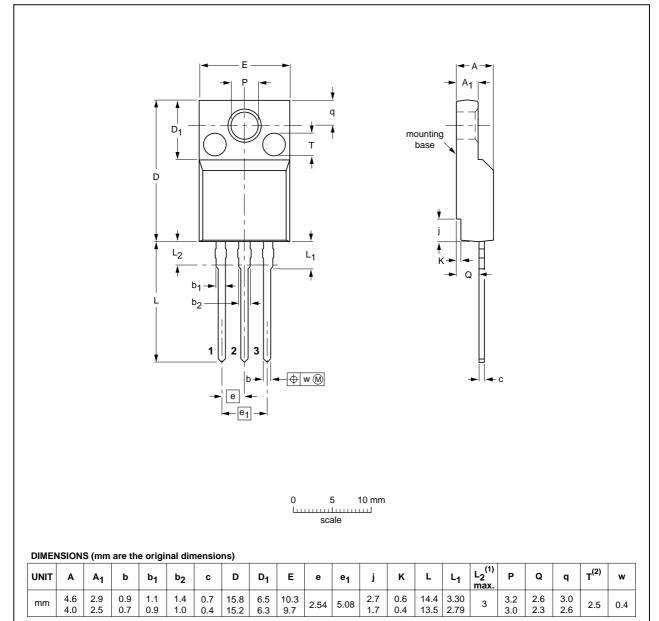
Epoxy meets UL94 V-0 at 3.175 mm.

10. Package outline

Plastic single-ended package; isolated heatsink mounted;

1 mounting hole; 3-lead TO-220 'full pack'

SOT186A



Notes

- 1. Terminal dimensions within this zone are uncontrolled
- 2. Both recesses are \varnothing 2.5 \times 0.8 max. depth

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT186A		3-lead TO-220F				02-04-09 06-02-14

Fig 12. Package outline SOT186A (3-lead TO-220F)

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11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA312X_SER_B_C_2	20071217	Product data sheet	-	BTA312X_SER_B_C_1
Modifications:	 Section 1.4 Section 3 ° Section 4 ° Section 7 ° 		on page 1 updated. n page 2 updated. e 2 updated. n page 6 updated. " on page 7 updated.	
BTA312X_SER_B_C_1	20070411	Product data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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